

### 40V DUAL NPN SMALL SIGNAL TRANSISTOR IN SOT563

### **Features**

- BV<sub>CEO</sub> > 40V
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Complementary PNP Type: MMDT2907V
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish. Solderable per MIL-STD-202, Method 208 (§3)
- Weight: 0.003 grams (Approximate)

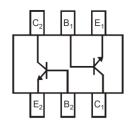
#### **SOT563**



Top View



**Bottom View** 



Device Schematic Top View

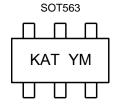
### Ordering Information (Note 4)

Product	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMDT2222V-7	Active	AEC-Q101	KAT	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**



KAT = Product Type Marking Code YM = Date Code Marking Y = Year (ex: A = 2013) M = Month (ex: 9 = September)

#### Date Code Key

Year	2013		2014	2015		2016	2017		2018	2019		2020
Code	Α		В	С		D	E		F	G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	2	1	5	6	7	8	9	0	N	D



# Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	75	V
Collector-Emitter Voltage	$V_{CEO}$	40	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	Ic	600	mA

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	150	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0</sub> JA	833	°C/W
Operating and Storage and Temperature Range	TJ, TSTG	-55 to +150	°C

### ESD Ratings (Note 6)

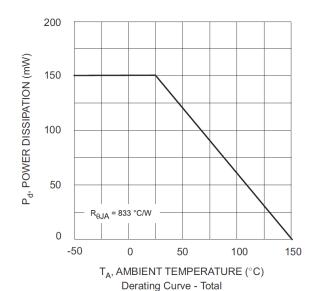
Notes:

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

# **Thermal Characteristic and Derating Information**





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

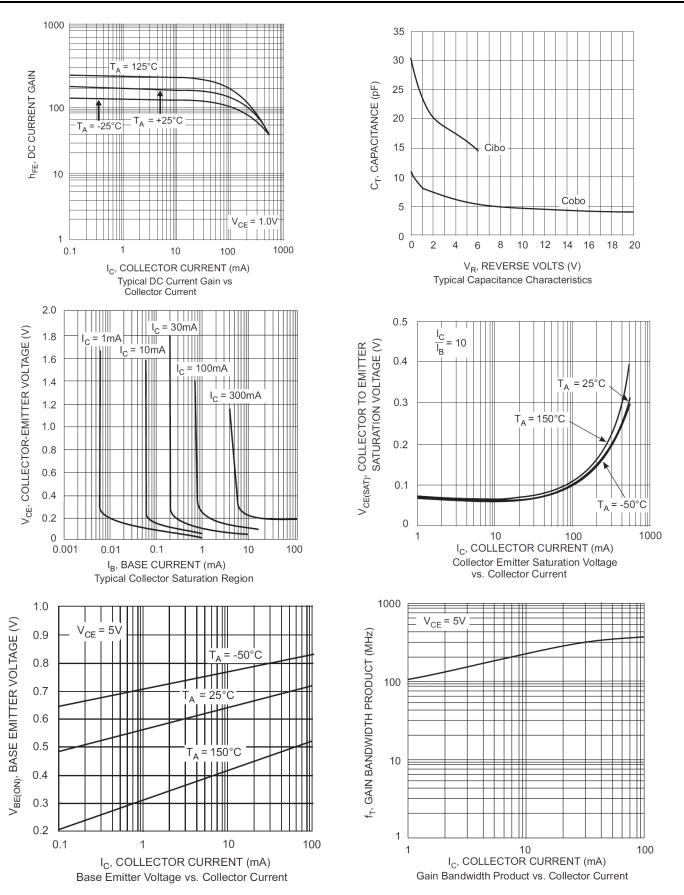
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	$BV_{CBO}$	75		V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage (Note 7)	$BV_{CEO}$	40		V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6.0		V	$I_E = 100 \mu A, I_C = 0$
Collector-Base Cut-Off Current	I <sub>CBO</sub>		10	nΑ μΑ	$V_{CB} = 60V, I_E = 0$ $V_{CB} = 60V, I_E = 0, T_A = +150$ °C
Collector Cut-Off Current	I <sub>CEX</sub>	_	10	nA	VcE = 60V, VBE(OFF) = 3.0V
Emitter-Base Cut-Off Current	I <sub>EBO</sub>	_	10	nA	$V_{EB} = 3V, I_{C} = 0$
Base Cut-Off Current	I <sub>BL</sub>	_	20	nA	$V_{CE} = 60V$ , $V_{BE(OFF)} = 3.0V$
ON CHARACTERISTICS (Note 7)				·	. ==(0.1.7
DC Current Gain	h <sub>FE</sub>	35 50 75 100 40 50 35	300	_	I <sub>C</sub> = 100µA, V <sub>CE</sub> = 10V I <sub>C</sub> = 1.0mA, V <sub>CE</sub> = 10V I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V I <sub>C</sub> = 150mA, V <sub>CE</sub> = 10V I <sub>C</sub> = 500mA, V <sub>CE</sub> = 10V I <sub>C</sub> = 10mA, V <sub>CE</sub> = 10V
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	0.3 1.0	V	I <sub>C</sub> = 150mA, V <sub>CE</sub> = 1.0V I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.6	1.2 2.0	٧	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{obo}$	_	8.0	pF	$V_{CB} = 10V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>ibo</sub>	_	25	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_{C} = 0$
Current Gain-Bandwidth Product	f⊤	300	_	MHz	$V_{CE} = 20V, I_{C} = 20mA,$ f = 100MHz
Noise Figure	NF		4.0	dB	$V_{CE} = 10V, I_{C} = 100\mu A,$ $R_{S} = 1.0k\Omega, f = 1.0kHz$
SWITCHING CHARACTERISTICS					
Delay Time	t <sub>d</sub>	_	10	ns	$V_{CC} = 30V, I_C = 150mA,$
Rise Time	tr		25	ns	$V_{BE(off)} = -0.5V, I_{B1} = 15mA$
Storage Time	t <sub>s</sub>		225	ns	V <sub>CC</sub> = 30V, I <sub>C</sub> = 150mA,
Fall Time	t <sub>f</sub>	_	60	ns	$I_{B1} = I_{B2} = 15\text{mA}$

Note:

<sup>7.</sup> Measured under pulsed conditions. Pulse width  $\leq 300 \mu s.$  Duty cycle  $\leq 2\%.$ 



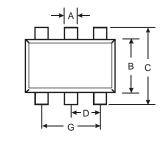
# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

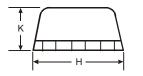


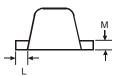


# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.



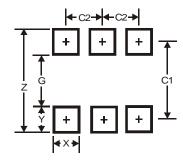




	SOT563						
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	0.55	0.60	0.60				
L	0.10	0.30	0.20				
M	0.10	0.18	0.11				
All	All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	SOT563
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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